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(72)Inventor: NIIJIMA HIDETO

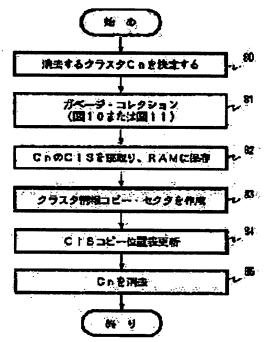
TOYOOKA TAKASHI

(54) BATCH ERASURE TYPE NON-VOLATILE MEMORY

(57)Abstract:

PURPOSE: To enhance resistance against fault like power cutoff, etc., in a semiconductor disk device which uses a batch erasure type nonvolatile memory.

CONSTITUTION: A batch erasure type nonvolatile memory contains plural sectors and attribute information for recognizing their own attribute is written in every sector. As a rule, a cluster information sector is placed at the front position of a cluster to which it belongs. Then, data sector is placed in a data area which is an area except the front position of a cluster. A controller connected to the memory produces a cluster information copy sector in a data are at the time of cluster erasure, reconstitutes cluster management information from the cluster



information copy sector and produces a cluster information sector at the time of cluster initialization.

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